# **1.5 A, 30 V, Schottky** Barrier Diode

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current and are offered in a Chip Scale Package (CSP) to reduce board space. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

#### Features

- Low Forward Voltage Drop 530 mV (Typ.) @  $I_F$  = 1.5 A
- Low Reverse Current  $20 \,\mu A$  (Typ.) @ V<sub>R</sub> =  $30 \,V$
- 1.5 A of Continuous Forward Current
- ESD Rating Human Body Model: Class 3B
  - Machine Model: Class C
- High Switching Speed
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

#### MAXIMUM RATINGS

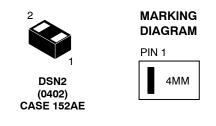
Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Current (DC)	١ <sub>F</sub>	1.5	А
Forward Surge Current (60 Hz @ 1 cycle)	I <sub>FSM</sub>	12	A
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I <sub>FRM</sub>	2.5	A
ESD Rating: Human Body Model Machine Model		> 8 > 400	kV V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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4M = Specific Device Code Y = Year Code

#### **PIN CONNECTIONS**

1 0 2 CATHODE ANODE

#### **ORDERING INFORMATION**

Device	Package	Shipping†
NSR15304NXT5G	DSN2 (Pb-Free)	5000 / Tape & Reel

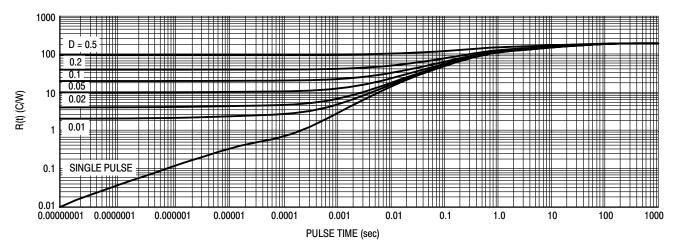
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ T <sub>A</sub> = 25°C	$R_{ heta JA}$ $P_D$			260 480	°C/W mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T <sub>A</sub> = 25°C	R <sub>θJA</sub> P <sub>D</sub>			100 1.25	°C/W W
Storage Temperature Range	T <sub>stg</sub>			-40 to +125	°C
Junction Temperature	TJ			+150	°C

1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

2. Mounted onto a 4 in square FR-4 board 650 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.





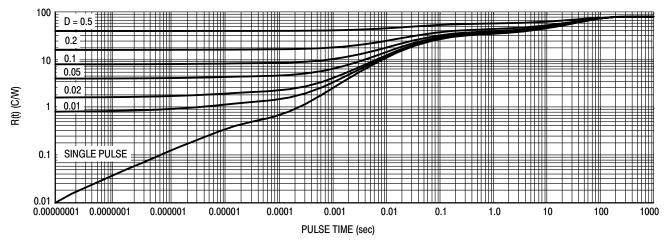
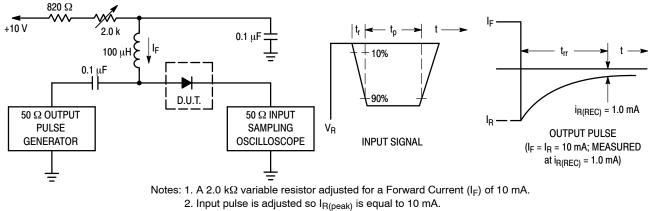


Figure 2. Thermal Response (Note 2)

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage $(V_R = 10 V)$ $(V_R = 30 V)$	I <sub>R</sub>		2.0 20	10 80	μΑ
Forward Voltage $(I_F = 10 \text{ mA})$ $(I_F = 100 \text{ mA})$ $(I_F = 500 \text{ mA})$ $(I_F = 1.0 \text{ A})$ $(I_F = 1.5 \text{ A})$	VF	- - - - -	270 340 420 480 530	310 380 460 520 580	mV
Total Capacitance (V <sub>R</sub> = 2.0 V, f = 1.0 MHz)	CT	-	60	-	pF
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mA, I <sub>R(REC)</sub> = 1.0 mA, Figure 3)	t <sub>rr</sub>	-	25	-	ns
Peak Forward Recovery Voltage ( $I_F$ = 100 mA, $t_r$ = 20 ns, Figure 4)	V <sub>FRM</sub>	-	492	-	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.







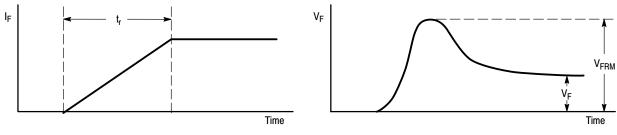
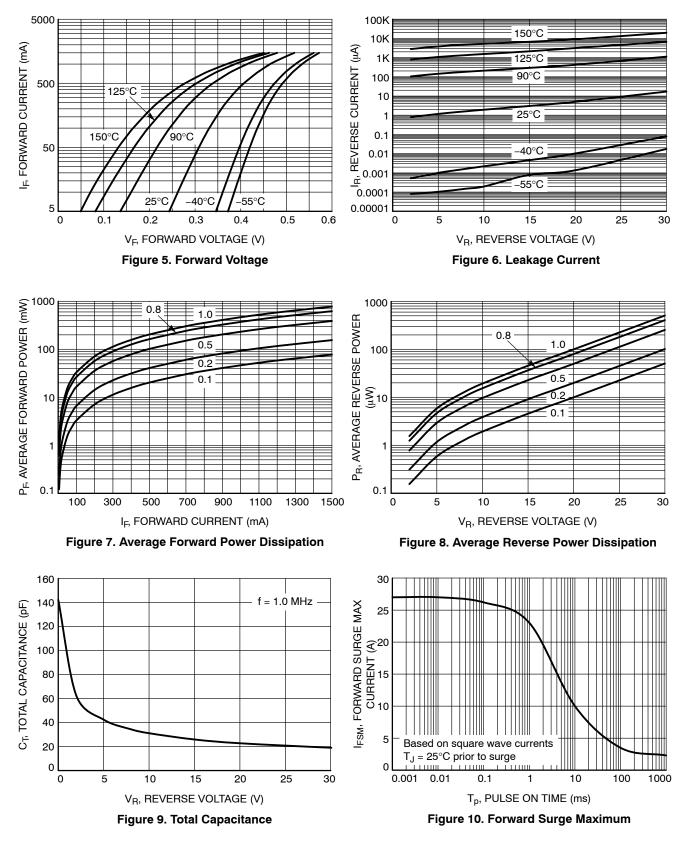
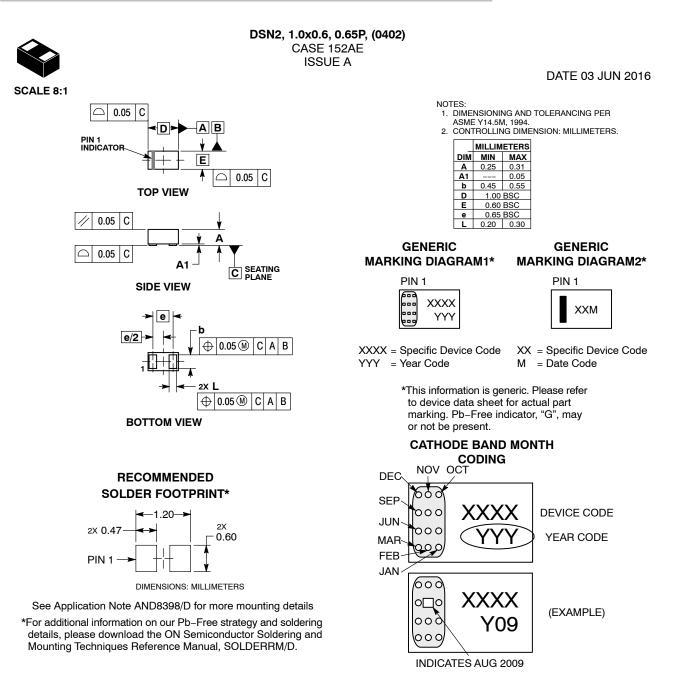


Figure 4. Peak Forward Recover Voltage Definition

#### **TYPICAL CHARACTERISTICS**







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